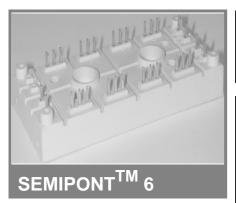
SKD 146/..-L100



3-Phase Bridge Rectifier+ IGBT braking chopper

SKD 146/..-L100

Target Data

Features

- · Compact design
- · Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- UL recognized, file no. E 63 532

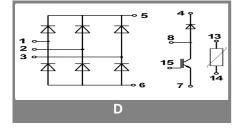
Typical Applications

- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger

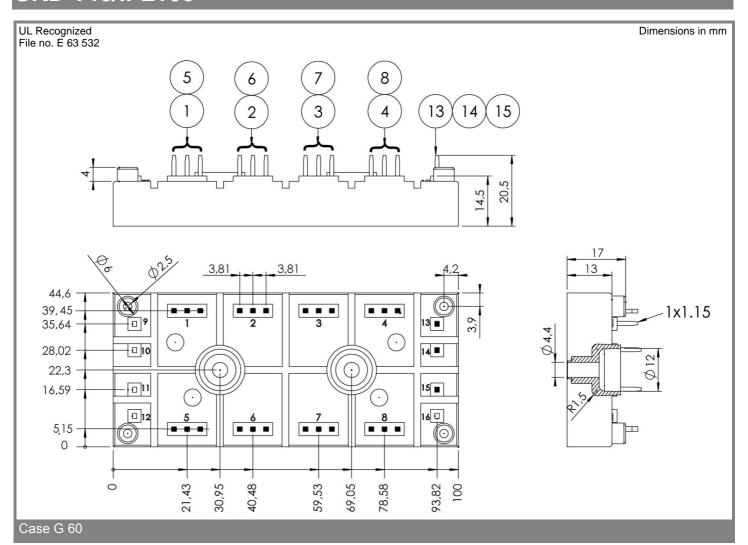
V_{RSM}	V_{RRM}, V_{DRM}	I _D = 140 A (maximum value for continuous operation)		
V	V	(T _s = 85 °C)		
1300	1200	SKD 146/12-L100		
1700	1600	SKD 146/16-L100		

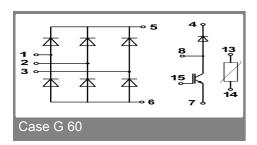
Absolute	Maximum Ratings	T _s = 25 °C, unless otherwise s	T _s = 25 °C, unless otherwise specified				
Symbol	Conditions	Values	Units				
Bridge - Rectifier							
I _D	T _s = 85 °C; inductive load	140	Α				
I_{FSM}/I_{TSM}	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	1250	Α				
i²t	$t_p = 10 \text{ ms}; \sin 180^\circ; T_{jmax}$	7800	A²s				
IGBT - Chopper							
V_{CES}/V_{GES}		1200 / 20	V				
I _C	T _s = 25 (70) °C	125 (100)	Α				
I _{CM}	$t_p = 1 \text{ ms; } T_s = 25 (70) ^{\circ}\text{C}$	250 (200)	Α				
Freewhee	eling - CAL Diode		•				
V_{RRM}		1200	V				
I _F	T _s = 25 (70) °C	130 (90)	Α				
I _{FM}	t _p = 1 ms; T _s = 25 (70) °C	240 (180)	Α				
T_{v_i}	Diode & IGBT (Thyristor)	- 40 + 150 (0 + 125)	°C				
T _{stg}		- 40 + 125	°C				
T _{solder}	terminals, 10 s	260	°C				
V_{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V				

Characteristics		$T_s = 25 ^{\circ}C$	T_s = 25 °C, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units		
Diode - Rectifier							
V_{TO} / r_{t}	T _j = 125 °C		0,8 / 4		V / $m\Omega$		
$R_{th(j-s)}$	per diode			0,8	K/W		
IGBT - Chopper							
V _{CE(sat)}	I _C = 100 A, T _j = 25 °C; V _{GE} = 15 V		2,35		V		
$R_{th(j-s)}$	per IGBT			0,3	K/W		
t _{d(on)} / t _r	valid for all values:		70 / 50		ns		
t _{d(off)} / t _f	V_{CC} = 600 V; V_{GE} = 15 V; I_{C} = 100 A; T_{j} = 125 °C;		450 / 45		ns		
$E_{on} + E_{off}$	$T_{j} = 125 ^{\circ}\text{C}; R_{G} = 7 \Omega;$		25		mJ		
	inductive load						
CAL - Did	ode - Freewheeling				•		
$V_{T(TO)} / r_t$	T _j = 125 °C		1 / 8	1,2 / 11	V / $m\Omega$		
$R_{th(j-s)}$	per diode			0,6	K/W		
I _{RRM}	valid for all values:		65		Α		
Q _{rr}	$I_F = 100 \text{ A; } V_R =600 \text{ V;} $ $dI_F/dt =1000 \text{ A/}\mu\text{s}$		15		μC		
E _{off}	V _{GE} = 0 V; T _j = 125 °C				mJ		
Tempera	ture Sensor	·			•		
R _{TS}	T = 25 (100) °C;		1000 (1670)		Ω		
Mechanical data							
M_S	mounting Torque	2,5		3,5	Nm		



SKD 146/..-L100





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

2 07-10-2004 SCT © by SEMIKRON